

IN THE CLAIMS:

Amendments to the Claims

Please cancel claims 52-61 without prejudice or disclaimer of the subject matter thereof and add the new claims as shown below.

Listing of Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-61 (canceled)

62. (new) A plasma etching apparatus for etching processing of a sample which is disposed inside of an etching chamber in which a processing gas is supplied by using a plasma generated inside of the etching chamber, comprising:

a detachable member which is detachably held against a sidewall of the etching chamber inside of the etching chamber and which forms an inner surface of the etching chamber which is in contact with the plasma, the detachable member being removable from the sidewall to outside of the etching chamber; and

a thermally conductive medium which is circulated inside of the detachable member so as to control a temperature of a surface of the detachable member during etching processing of the sample so that products formed in the etching chamber during the etching processing of the sample are deposited and maintained on the detachable member.

63. (new) A plasma etching apparatus according to claim 62, wherein the surface of the detachable member is controlled to a temperature within a range of 20°C to 100°C.

64. (new) A plasma etching apparatus according to claim 62, wherein the surface of the detachable member is controlled to a temperature lower than a temperature of the sample.

65. (new) A plasma etching apparatus according to claim 62, wherein the sidewall and the detachable member are formed of metal.

66. (new) A plasma etching apparatus for etching processing of a sample which is disposed inside of an etching chamber in which a processing gas is supplied by using a plasma generated inside of the etching chamber, comprising:

a detachable member which is detachably held against a sidewall of the etching chamber inside of the etching chamber and which forms an inner surface of the etching chamber which is in contact with the plasma, the detachable member being removable from the sidewall to outside of the etching chamber and being supplied with a thermally conductive medium circulated inside of the detachable member; and

a temperature controller for adjusting the thermally conductive medium so as to control a temperature of a surface of the detachable member during etching processing of the sample so that products formed in the etching chamber during the etching processing of the sample are deposited and maintained on the detachable member.

67. (new) A plasma etching apparatus according to claim 66, wherein the surface of the detachable member is controlled to a temperature within a range of 20°C to 100°C.

68. (new) A plasma etching apparatus according to claim 66, wherein the surface of the detachable member is controlled to a temperature lower than a temperature of said sample.

69. (new) A plasma etching apparatus according to claim 66, wherein the sidewall and the detachable member are formed of metal.